

DS-02-017

October 6, 2003



To: Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/615,124 07/08/03

Horst Knoedgen

NATURAL ANALOG OR MULTILEVEL
TRANSISTOR DRAM-CELL

Grp. Art Unit:

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.


The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56. Copies of each document is included herewith.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on October 10, 2003.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 10/10/03

U.S. Patent 6,373,767 to Patti, "Memory That Stores Multiple Bits Per Storage Cell," describes a multi-level memory in which each storage cell stores multiple bits.

U.S. Patent 6,282,115 to Furukawa et al., "Multi-Level DRAM Trench Store Utilizing Two Capacitors and Two Plates," discloses a multi-level memory cell capable of storing two or three bits of digital data occupying only four lithographic squares and requiring only one or two logic level voltage sources, respectively.

U.S. Patent 4,335,450 to Thomas, "Non-Destructive Read Out Field Effect Transistor Memory Cell System," describes a non-destructive read out memory cell system having a semiconductor substrate supporting an array of memory cells each of which includes a field effect transistor having a source and a drain defining a channel region having high and low threshold sections.

Sincerely,

A handwritten signature in black ink, appearing to read 'SBA', is written over the printed name.

Stephen B. Ackerman,
Reg. No. 37761

